

Rev.B Jul.-2026

TO-252 SiC N MOS

SiC N-CHANNEL MOSFET in a TO-252 Plastic Package.

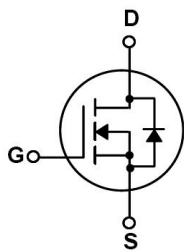
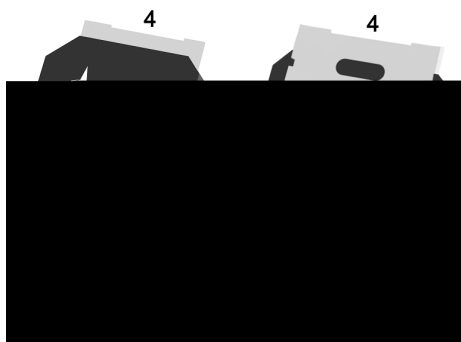
$V_{DS}=800V$ $I_D=7A$

$R_{DS(on)}@15V \leq 650m\Omega$ (Type. 500m Ω)

$R_{DS(on)}@18V \leq 600m\Omega$ (Type. 378m Ω)

LED PD PC

LED driver, PD charger, PC adapter, Air-conditioning, E-bike charger.



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

See Marking Instructions.

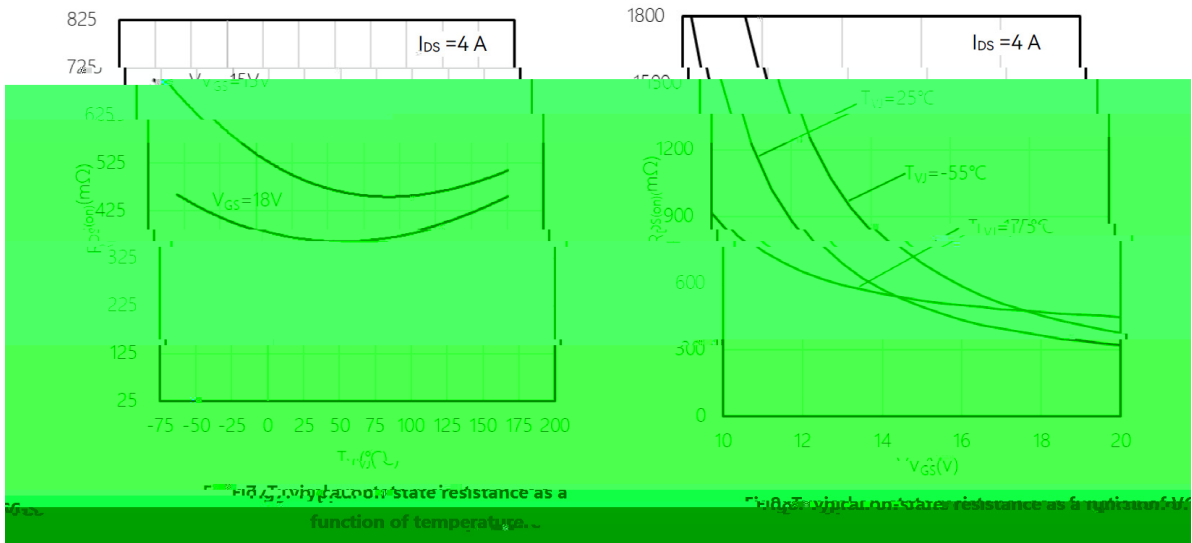
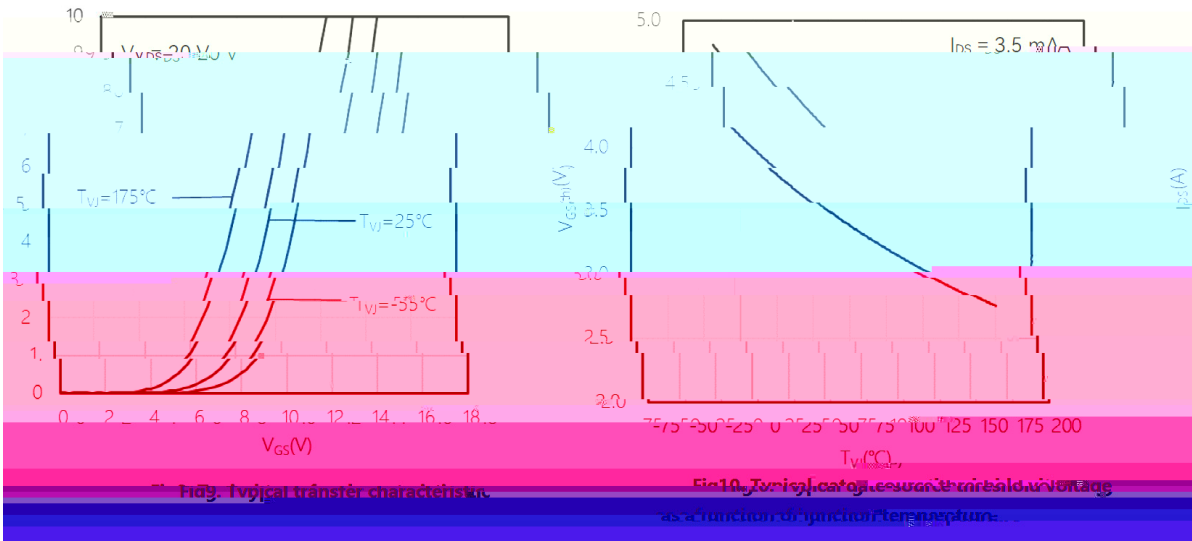
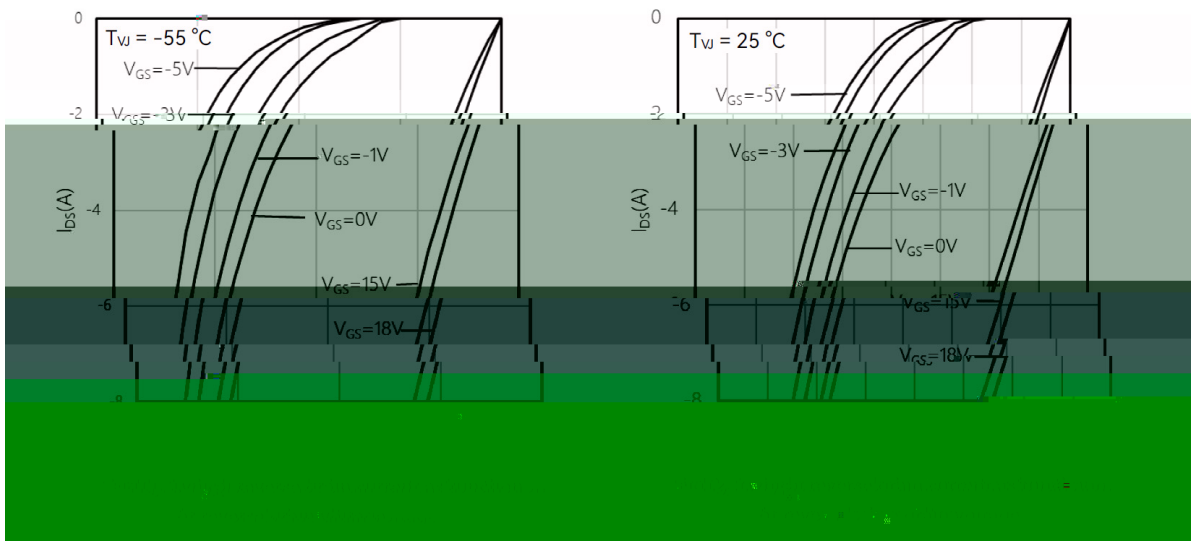
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	800	V
Continuous DC Drain Current for $R_{th(j-c,typ.)}$, Limited by $T_{VJ(max)}$	$I_D(T_c=25^\circ C)$	7	A
	$I_D(T_c=100^\circ C)$	5.7	A
Peak Drain Current, t_p Limited by $T_{VJ(max)}$	I_{DM}	12	A
Gate-Source Max Voltage	$V_{GS,max}$	-10/+22	V
Gate-Source Operate Voltage	$V_{GS,op}$	0/+15	V
Single Pulse Avalanche Energy	E_{AS}	10.2	mJ
Power Dissipation or $R_{th(j-c,typ.)}$	P_D		

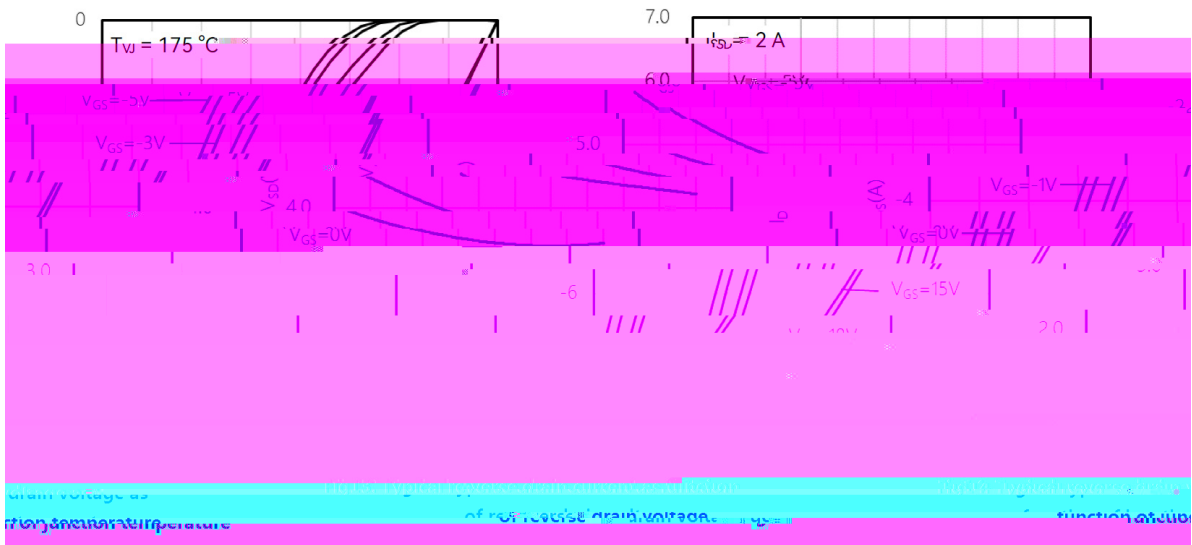
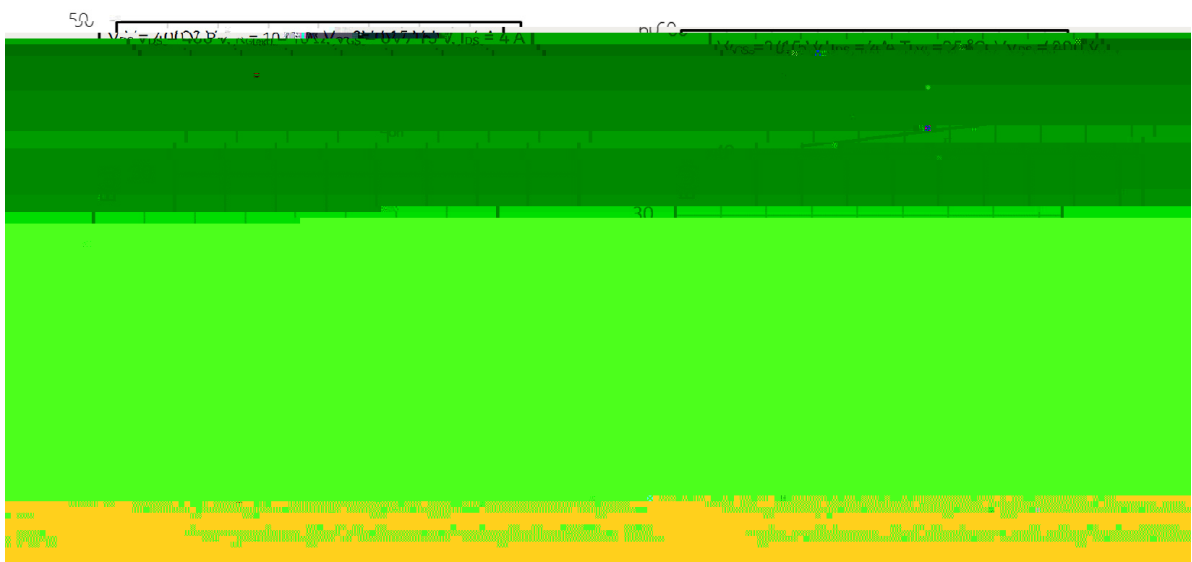
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=0/15V$ $L=600\mu H$ $V_{DD}=400V$ $I_D=4A$ $R_g=10\Omega$		16.1		ns
Turn-On Rise Time	t_r			13.9		
Turn-Off Delay Time	$t_{d(off)}$			13.3		
Turn-Off Fall Time	t_f			13.7		
Turn-On Switching Loss	E_{on}			41.2		μJ
Turn-Off Switching Loss	E_{off}			3.1		

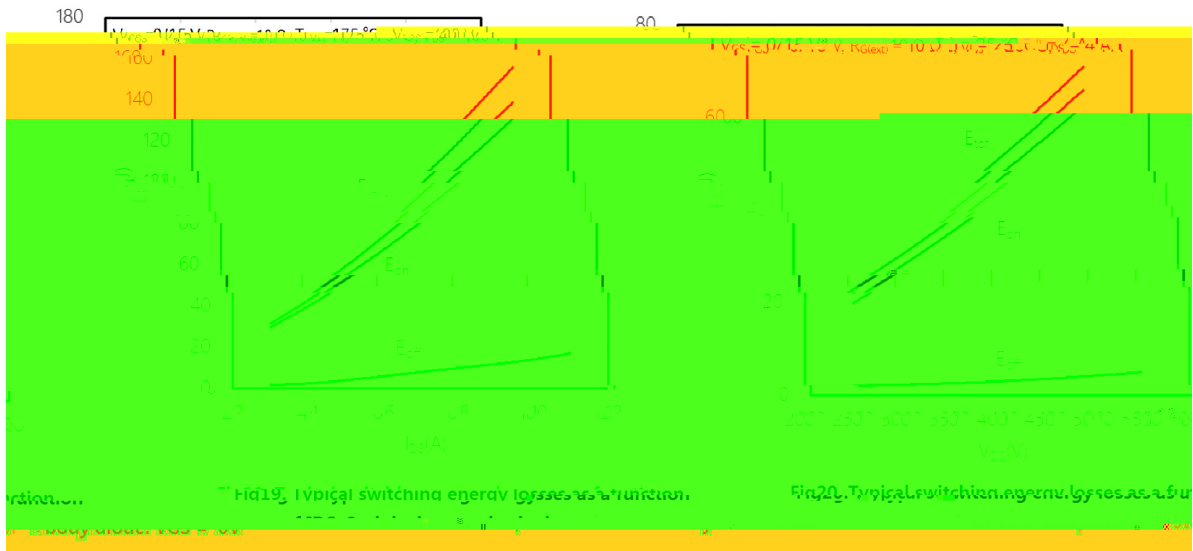
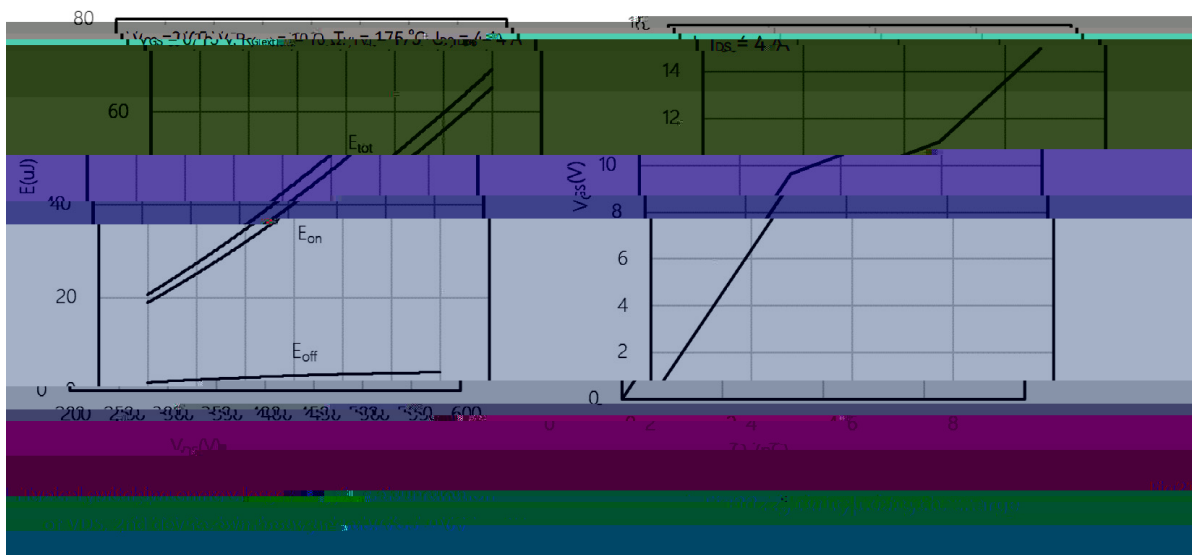
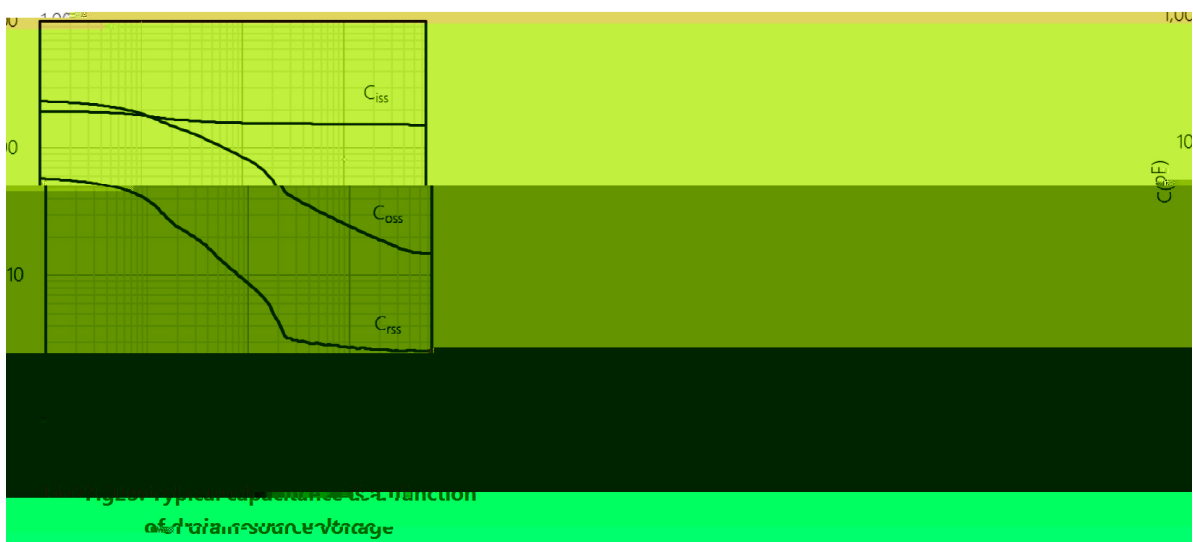
Total Switching Energy

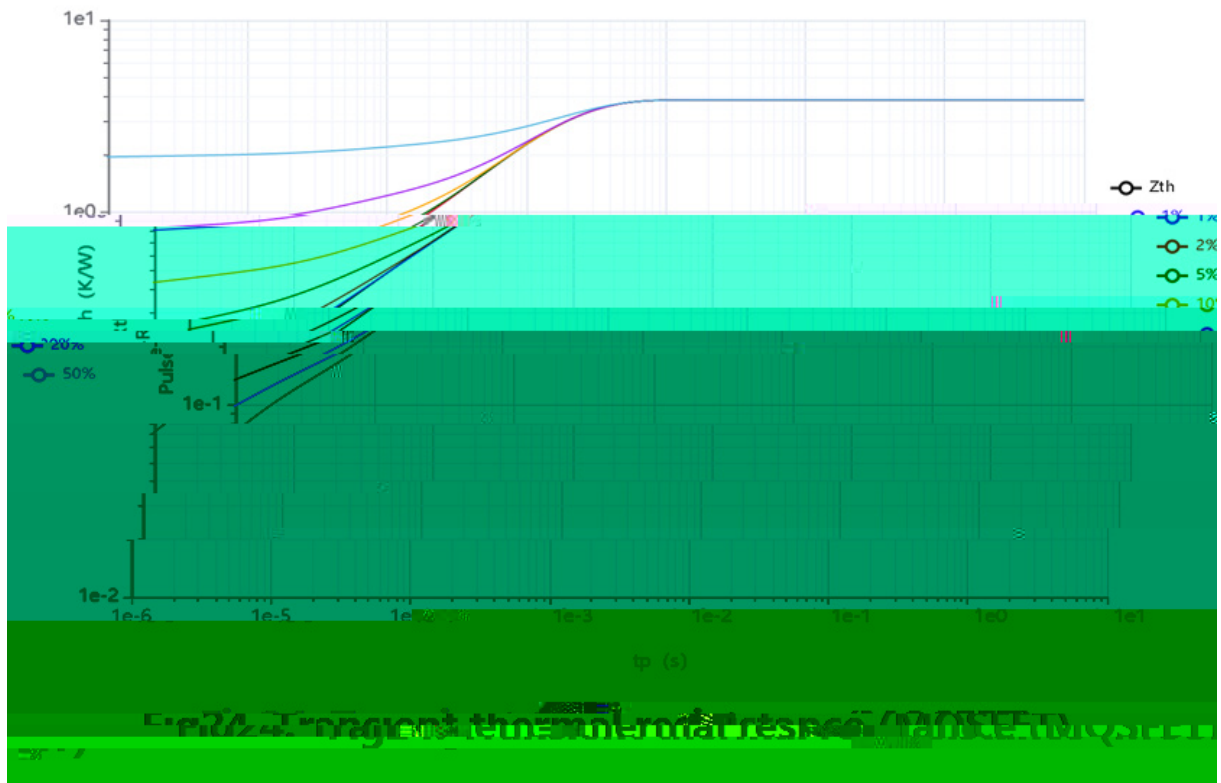
E_{TM} 76 572.18 .48001 18.42 ref539.22 tching Energy

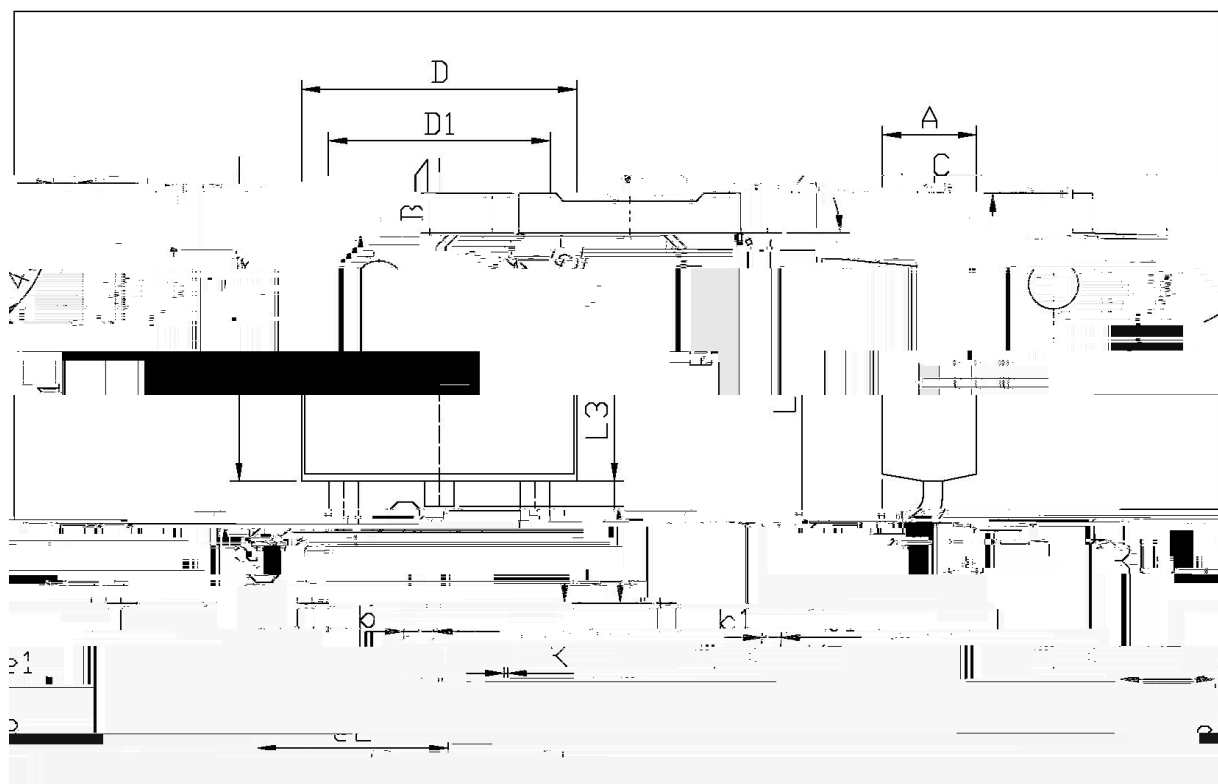
05EV6574TG00WrrHBT4621PDC01 yHT8







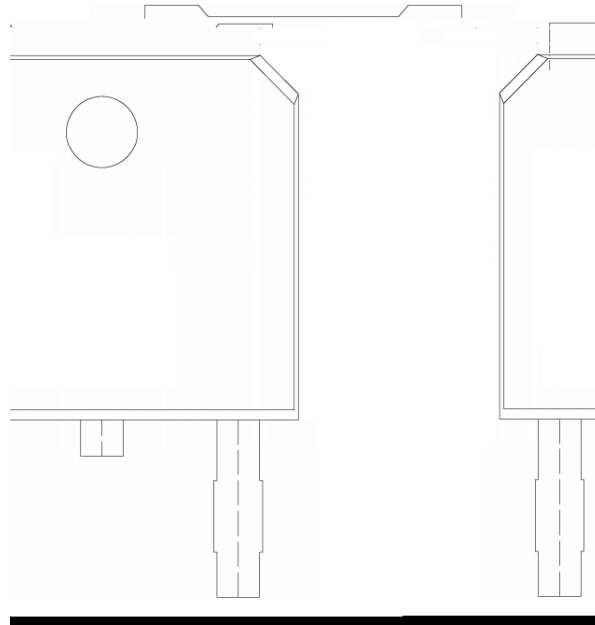




单位: mm

Technical drawing of a mechanical part, showing dimensions and tolerances. The drawing includes a cross-section view on the left and a side view on the right. Key dimensions include diameters (e.g., 1.25, 1.00, 0.95), lengths (e.g., 2.34, 2.24, 4.43), and specific features like a keyway and a threaded section. The drawing is labeled with 'DIN 913' and 'DIN 914'.

T0-252



Temperature Profile for IR Reflow Soldering(Pb-Free)
